

AMENDMENTS TO THE SPECIFICATION

Please amend paragraph 6 as follows:

[0006] In accordance with another aspect of the invention, a device, such as a stent, is provided having a surface and a TiN_xC_y compound deposited on at ~~least~~ least a region of the surface of the device. In accordance with another aspect of the invention, a device, such as a stent, is provided having a surface and a TiN_xC_y compound implanted at a depth within at least a region of the surface of the stent.

Please amend paragraph 19 as follows:

[0019] Surface modification can be accomplished by introducing argon in the reaction chamber and initiating plasma to sputter titanium off the grid and on or into surface 16. A source gas containing oxygen and nitrogen can also be introduced into the reaction chamber for reacting with the titanium to ~~from~~ form TiN_xC_y . By the way of example, in an embodiment in which the source gas nitrogen monoxide (NO), NO^- ions will react with titanium ions to form a titanium nitride monoxide (TiNO). Similarly, in an embodiment in which the source gas is nitrogen dioxide (NO_2), NO_2^- ions and dissociated NO^- ions will mix with titanium ions to form a mixture of titanium nitride dioxide (TiNO_2) and titanium nitride monoxide (TiNO). Windecker et al. has reported that coronary artery stents coated with titanium nitride monoxide reduced neointimal hyperplasia in pigs by 47% and 44%, respectively.

Please amend paragraph 21 as follows:

[0021] The negative voltage applied to stent 10 can have a frequency of up to, for example, 500 KHz and a width of 70 to about 200 microseconds. In one embodiment, as illustrated in Figure 2C1, a TiN_xO_y layer 22 is formed on the nitrogen or titanium region 20. In accordance with another embodiment, the nitrogen gas can be introduced into the chamber prior to the introduction of the combination of the oxygen and nitrogen gases. Accordingly, region 20 may include traces of TiN or alternatively, as illustrated in Figure 2C2, a layer of TiN, as illustrated by reference number 24, may be implanted in surface 16 followed by formation of TiN_xO_y deposited on surface 16, as illustrated by region 22a. Region 22b can be from about 500 Å to about 2000 Å in depth. As is understood by one

of ordinary skill in the art, a variety of modifications can be made to the process parameters so as to achieve a particular cross-sectional topography.

Please amend paragraph 23 as follows:

[0023] The above-described methods can be performed by any suitable apparatus known to one of ordinary skill in the art. ~~On~~ One example of such plasma reaction chamber 30 is illustrated in Figure 3. Chamber 30 can be cylindrical in shape and can be fabricated from any number of suitable materials, such as, stainless steel, glass, and aluminum. By way of example, chamber 30 can be from about 4 inches (10.16 cm) to about 15 inches (38.1 cm) in diameter and from about 5 inches (12.7 cm) to about 18 inches (45.72 cm) in height.